# MCH6431

## Power MOSFET 30V, 55mΩ, 5A, Single N-Channel



www.onsemi.com

#### **Features**

- Low On-Resistance
- 4V Drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance

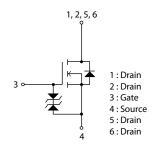
VDSS	R <sub>DS</sub> (on) Max	ID Max	
	55mΩ@ 10V		
30V	91mΩ@ 4.5V	5A	
	109mΩ@ 4V		

## **Specifications**

**Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V <sub>DSS</sub>	30	V
Gate to Source Voltage	VGSS	±20	٧
Drain Current (DC)	ID	5	Α
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	IDP	20	А
Power Dissipation When mounted on ceramic substrate (1200mm² × 0.8mm)	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

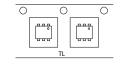
## Electrical Connection N-Channel



## **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit
Junction to Ambient			
When mounted on ceramic substrate	$R_{\theta JA}$	83.3	°C/W
(1200mm <sup>2</sup> × 0.8mm)			

Packing Type: TL Marking





Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

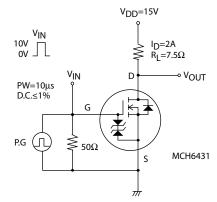
## MCH6431

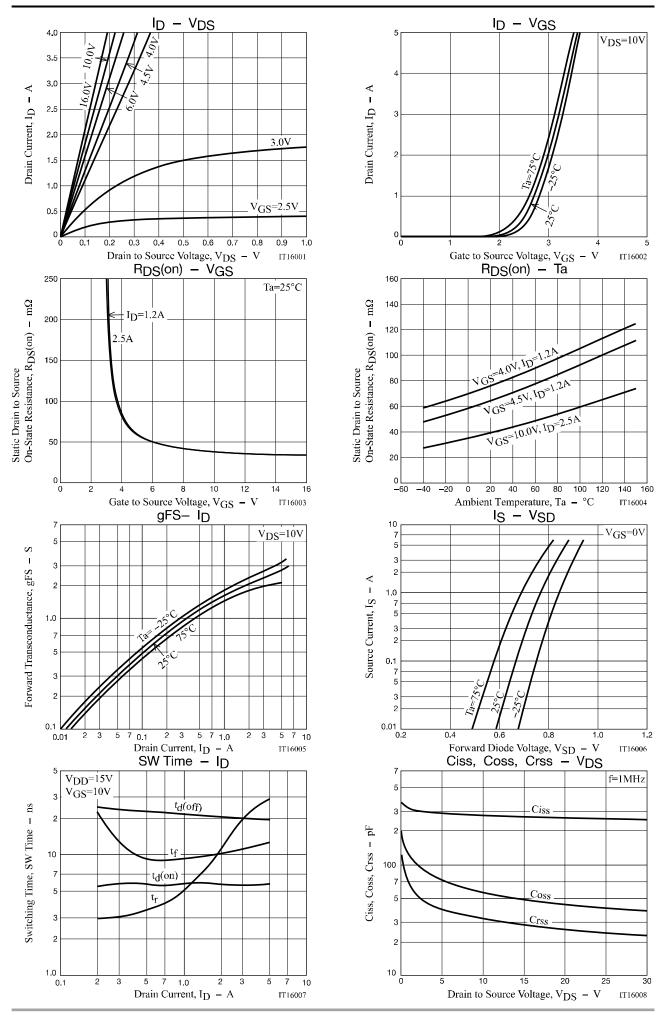
## **Electrical Characteristics** at Ta = 25°C

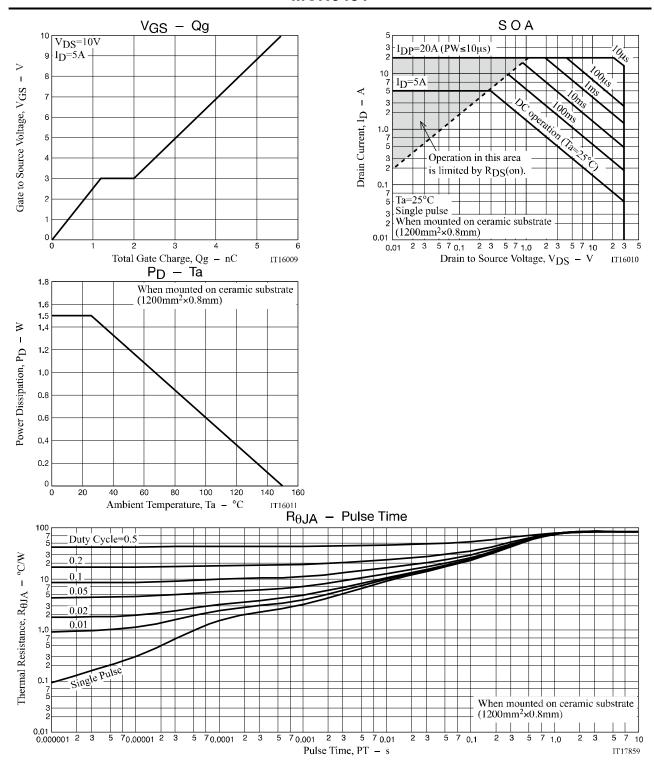
Parameter	Committee of	Conditions	Value			Unit
Parameter	Symbol		min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	٧
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =2.5A		2.2		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =2.5A, V <sub>GS</sub> =10V		42	55	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1.2A, V <sub>GS</sub> =4.5V		65	91	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =1.2A, V <sub>GS</sub> =4V		78	109	mΩ
Input Capacitance	Ciss			280		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss			30		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			5.7		ns
Rise Time	t <sub>r</sub>	On a constitut Total City II		11		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		21		ns
Fall Time	tf			10		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		1.2		nC
Gate to Drain "Miller" Charge	Qgd			0.8		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =5A, V <sub>GS</sub> =0V		0.85	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **Switching Time Test Circuit**







#### **Package Dimensions**

MCH6431-TL-H / MCH6431-TL-W

#### MCPH6

CASE 419AS ISSUE O

unit: mm

1: Drain

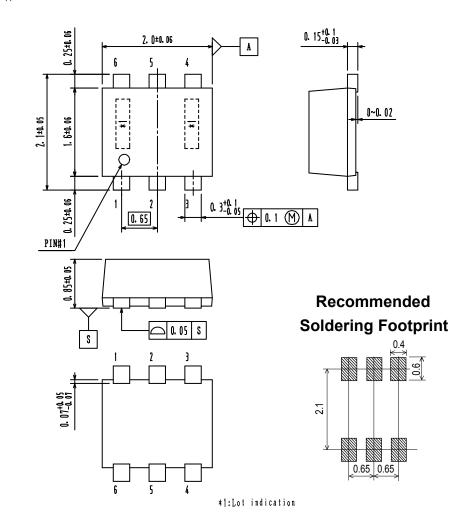
2: Drain

3: Gate

4 : Source

5: Drain

6: Drain



#### ORDERING INFORMATION

Device	Package	Shipping	Note
MCH6431-TL-H	MCPH6	MCPH6 3,000 pcs. / Tape & Reel Pb	Pb-Free
MCH6431-TL-W	SC-88FL,SC-70-6,SOT-363	3,000 pcs. / Tape & Neel	and Halogen Free

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6431 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent re